

DATASHEETL NPN SILICON TRANSISTOR

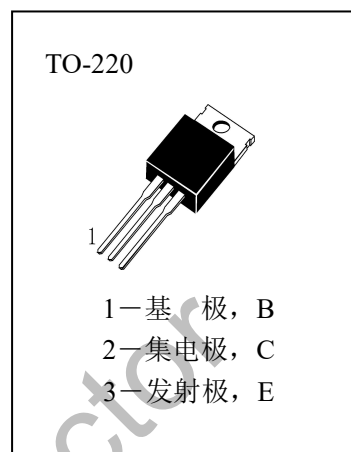
■ 主要用途

音频功率放大。

■ 极限值 (T_a=25℃)

T _{stg}	— 贮存温度	-55~150℃
T _j	— 结温	150℃
P _C	— 集电极功率耗散 (T _c =25℃)	65W
P _C	— 集电极功率耗散 (T _A =25℃)	2W
V _{CBO}	— 集电极—基极电压	100V
V _{CEO}	— 集电极—发射极电压	100V
V _{EBO}	— 发射极—基极电压	5V
I _C	— 集电极电流	6A
I _B	— 基极电流	2A

■ 外形图及引脚排列



■ 电参数 (T_a=25℃)

参数符号	符号说明	最小值	典型值	最大值	单位	测试条件
I _{CEO}	集电极—发射极截止电流			0.7	mA	V _{CE} =60V, I _B =0
I _{EBO}	集电极—基极截止电流			1	mA	V _{EB} =5V, I _C =0
I _{CES}	集电极—发射极饱和电流			400	μA	V _{CE} =100V, V _{EB} =0
HFE (1)	直流电流增益	30				V _{CE} =4V, I _C =0.3A
HFE (2)	直流电流增益	15		80		V _{CE} =4V, I _C =3A
V _{CE(sat)}	集电极—发射极饱和压降			1.5	V	I _C =6A, I _B =600mA
V _{BE(on)}	基极—发射极导通电压			2.0	V	V _{CE} =4V, I _C =6A
BV _{CEO}	集电极—发射极击穿电压	100			V	I _C =30mA, I _B =0
f _T	特征频率	3.0			MHz	V _{CE} =10V, I _C =500mA f=1MHz

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■ 典型特性曲线

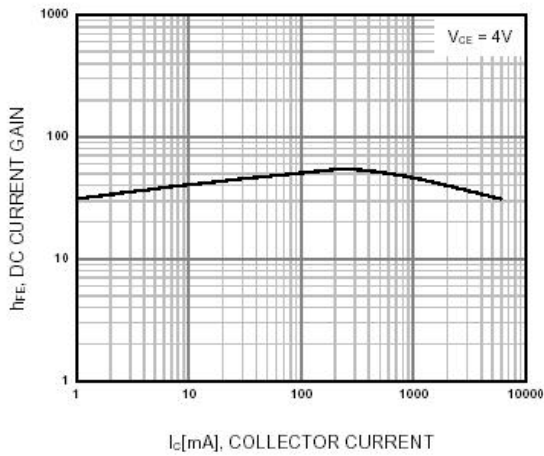


Figure 1. DC current Gain

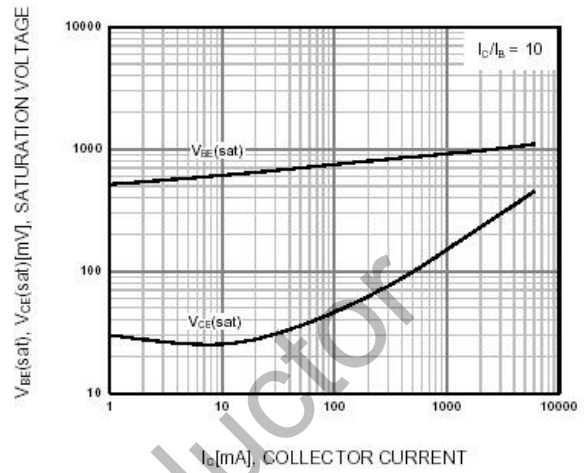


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

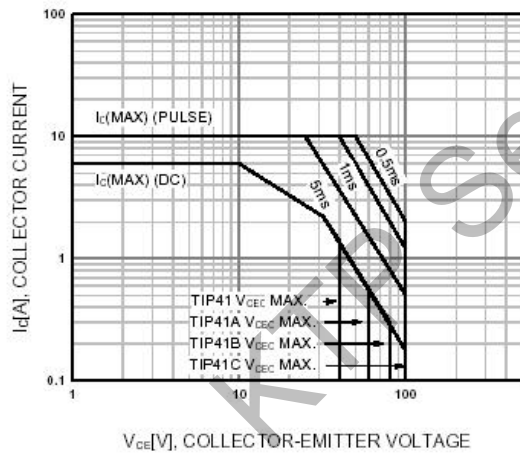


Figure 3. Safe Operating Area

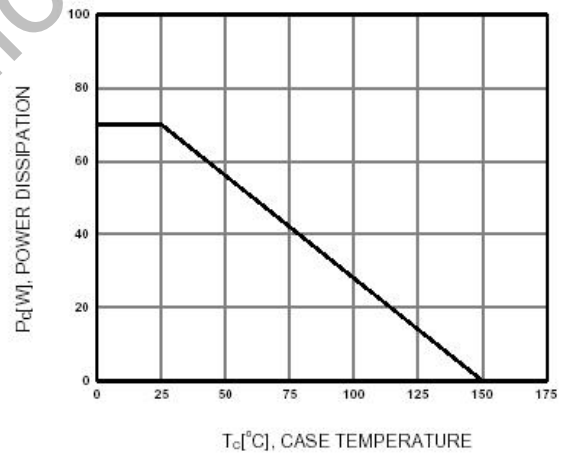


Figure 4. Power Derating